

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1.-17 (canceled)

18 (New) A manufacturing method for an SOI wafer, comprising:  
bonding an active layer wafer with a supporting wafer via an insulating film to form a bonded wafer body;  
reducing a film thickness in a part of the active layer wafer that forms a part of the bonded wafer body to form an SOI layer for manufacturing the SOI wafer, wherein the supporting wafer has a nitrogen concentration in a range of  $1 \times 10^{14}$  atoms/cm<sup>3</sup> to  $3 \times 10^{15}$  atoms/cm<sup>3</sup> and an oxygen concentration of equal to or higher than  $12 \times 10^{17}$  atoms/cm<sup>3</sup> when measured in accordance with old ASTM so as to have an oxidation induced stacking fault substantially entirely across a surface thereof.

19. (New) A manufacturing method for an SOI wafer, comprising:  
bonding an active layer wafer with a supporting wafer via an insulating film to form a bonded wafer body; and  
reducing a film thickness in a part of the active layer wafer that forms a part of the bonded wafer body to form an SOI layer for manufacturing the SOI wafer, wherein the supporting wafer has an oxygen concentration of equal to or higher than  $16 \times 10^{17}$  atoms/cm<sup>3</sup> when measured in accordance with old ASTM.

20. (New) The manufacturing method of an SOI wafer in accordance with claim 18, further comprising:

ion-implanting one of hydrogen gas and a noble gas element to the active layer wafer to form an ion-implanted layer in the active layer wafer, prior to said bonding; and heat treating the bonded wafer body to induce cleavage in the bonded wafer body at the site of the ion-implanted layer as an interface so as to form the SOI layer with a remaining active layer.

21. (New) The manufacturing method of an SOI wafer in accordance with claim 19, further comprising:

ion-implanting one of a hydrogen gas and a noble gas element to the active layer wafer to form an ion-implanted layer in the active layer wafer, prior to said bonding; and heat treating the bonded wafer body to induce cleavage in the bonded wafer at the site of the ion-implanted layer as an interface so as to form the SOI layer with a remaining active layer.

22. (New) The manufacturing method of an SOI wafer in accordance with claim 18, wherein a thickness of the SOI layer is thinner than  $0.10\mu\text{m}$ .

23. (New) The manufacturing method of an SOI wafer in accordance with claim 19, in which a thickness of the SOI layer is thinner than  $0.10\mu\text{m}$ .

24. (New) The manufacturing method of an SOI wafer in accordance with claim 20, wherein a thickness of the SOI layer is thinner than 0.10 $\mu$ m.

25. (New) The manufacturing method of an SOI wafer in accordance with claim 21, wherein a thickness of the SOI layer is thinner than 0.10 $\mu$ m.

26. (New) The manufacturing method of an SOI wafer in accordance with claim 18 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

27. (New) The manufacturing method of an SOI wafer in accordance with claim 19 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

28. (New) The manufacturing method of an SOI wafer in accordance with claim 20 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

29. (New) The manufacturing method of an SOI wafer in accordance with claim 21 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

30. (New) The manufacturing method of an SOI wafer in accordance with claim 22 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

31. (New) The manufacturing method of an SOI wafer in accordance with claim 23 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

32. (New) The manufacturing method of an SOI wafer in accordance with claim 24 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

33. (New) The manufacturing method of an SOI wafer in accordance with claim 25 further comprising one of:

applying a rapid thermal process at a temperature in a range of 1100 °C to 1250 °C for five minutes or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding; and

applying a high-temperature heat treatment at a temperature in a range of 1050 °C to 1250 °C for one hour or longer to the supporting wafer in a reducing gas atmosphere, prior to said bonding.

34. (New) An SOI wafer manufactured by the following method:

bonding an active layer wafer with a supporting wafer via an insulating film to form a bonded wafer body;

reducing a film thickness in a part of the active layer wafer that forms a part of the bonded wafer body to form an SOI layer for manufacturing the SOI wafer, wherein the supporting wafer has a nitrogen concentration in a range of  $1 \times 10^{14}$  atoms/cm<sup>3</sup> to  $3 \times 10^{15}$  atoms/cm<sup>3</sup> and an oxygen concentration of equal to or higher than  $12 \times 10^{17}$  atoms/cm<sup>3</sup> when measured in accordance with old ASTM so as to have an oxidation induced stacking fault entirely across a surface thereof; and a thickness of the SOI layer is thinner than 0.10µm.

35. (New) An SOI wafer manufactured by the following method:  
bonding an active layer wafer with a supporting wafer via an insulating film to  
form a bonded wafer body; and  
reducing a film thickness in a part of the active layer wafer that forms a part of the  
bonded wafer body to form an SOI layer for manufacturing the SOI wafer, wherein  
the supporting wafer has an oxygen concentration of equal to or higher than  
 $16 \times 10^{17}$  atoms/cm<sup>3</sup> when measured in accordance with old ASTM; and a thickness of the  
SOI layer is thinner than 0.10 $\mu$ m.